NSN 5961-01-031-7279

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View Online at https://aerobasegroup.com/nsn/5961-01-031-7279 **Inclosure Material:** Metal **Overall Length:** Between 1.330 inches and 1.450 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 1.031 inches and 1.062 inches **Thread Size:** 0.500 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 10.0 off-state voltage, peak and 35.0 off-state voltage, rms total and 5.0 gate voltage, dc **Current Rating Per Characteristic:** 2.00 amperes forward current, total rms of standard range and 50.00 amperes forward current, total rms megahertz **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnpn **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug **Specification Data:** 81349-mil-s-19500/204 government specification Shelf Life:

No

N/a

Unit Of Measure:

Demilitarization:

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